

## **DVM16R2L4/16G**

## 16GB - 240-Pin 2Rx4 Registered ECC DDR3 DIMM

Identification DVM16R2L4/16G 2Gx72

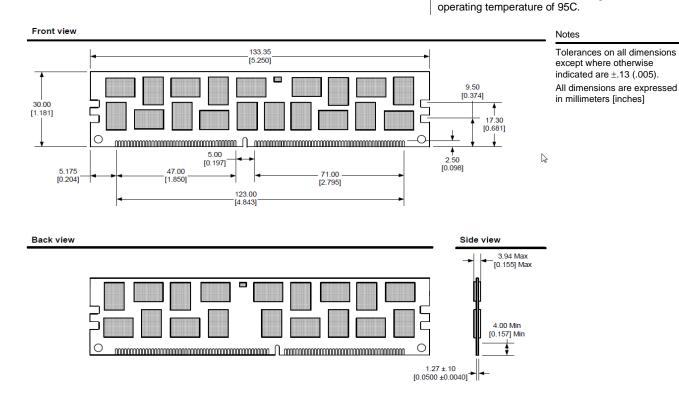
16GB 2Rx4 PC3L-12800R-11

## Performance Range

 $\frac{\text{Clock / Module Speed / CL-}t_{\text{RCD}}-t_{\text{RP}}}{800 \text{ MHz / PC3-}12800 / 11-11-11} \\ 667 \text{ MHz / PC3-}10600 / 10-10-10} \\ 667 \text{ MHz / PC3-}10600 / 9-9-9 \\ 533 \text{ MHz / PC3-}8500 / 8-8-8 \\ 533 \text{ MHz / PC3-}8500 / 7-7-7 \\ 400 \text{ MHz / PC3-}6400 / 6-6-6 \\ \end{array}$ 



Features	Description
240-pin JEDEC-compliant DIMM, 133.35 mm wide by 30.00 mm high Operating Voltage: VDD = VDDQ = +1.35V (1.283V to 1.45V)	<b>DVM16R2L4/16G</b> is a registered 2Gx72 memory module, which conforms to JEDEC's DDR3L,
Backward-compatible to VDD = $VDDQ = +1.5V (1.255V to 1.45V)$	PC3L-12800 standard. The assembly is Dual
I/O Type: SSTL_15	Rank. Each rank is comprised of eighteen 1Gbx4
On-board I <sup>2</sup> C temperature sensor with integrated Serial Presence-Detect (SPD) EEPROM	DDR3 SDRAMs.
Data Transfer Rate: 12.8 Gigabytes/sec	One FERROM is used for Oneigh Researce Refert
Data Bursts: 8 and burst chop 4 mode ZQ Calibration for Output Driver and On-Die Termination (ODT)	One EEPROM is used for Serial Presence Detect and a combination register/PLL, with Address and
Programmable ODT / Dynamic ODT during Writes	Command Parity, is also used.
Programmable CAS Latency: 6, 7, 8, 9, 10 and 11	
Bi-directional Differential Data Strobe signals	Both output driver strength and input termination
SDRAM Addressing (Row/Col/BG/BA): 16/11/3	impedance are programmable to maintain signal
Fully RoHS Compliant	integrity on the I/O signals in a Fly-by topology.
	A thermal sensor accurately monitors the DIMM module and can prevent exceeding the maximum



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